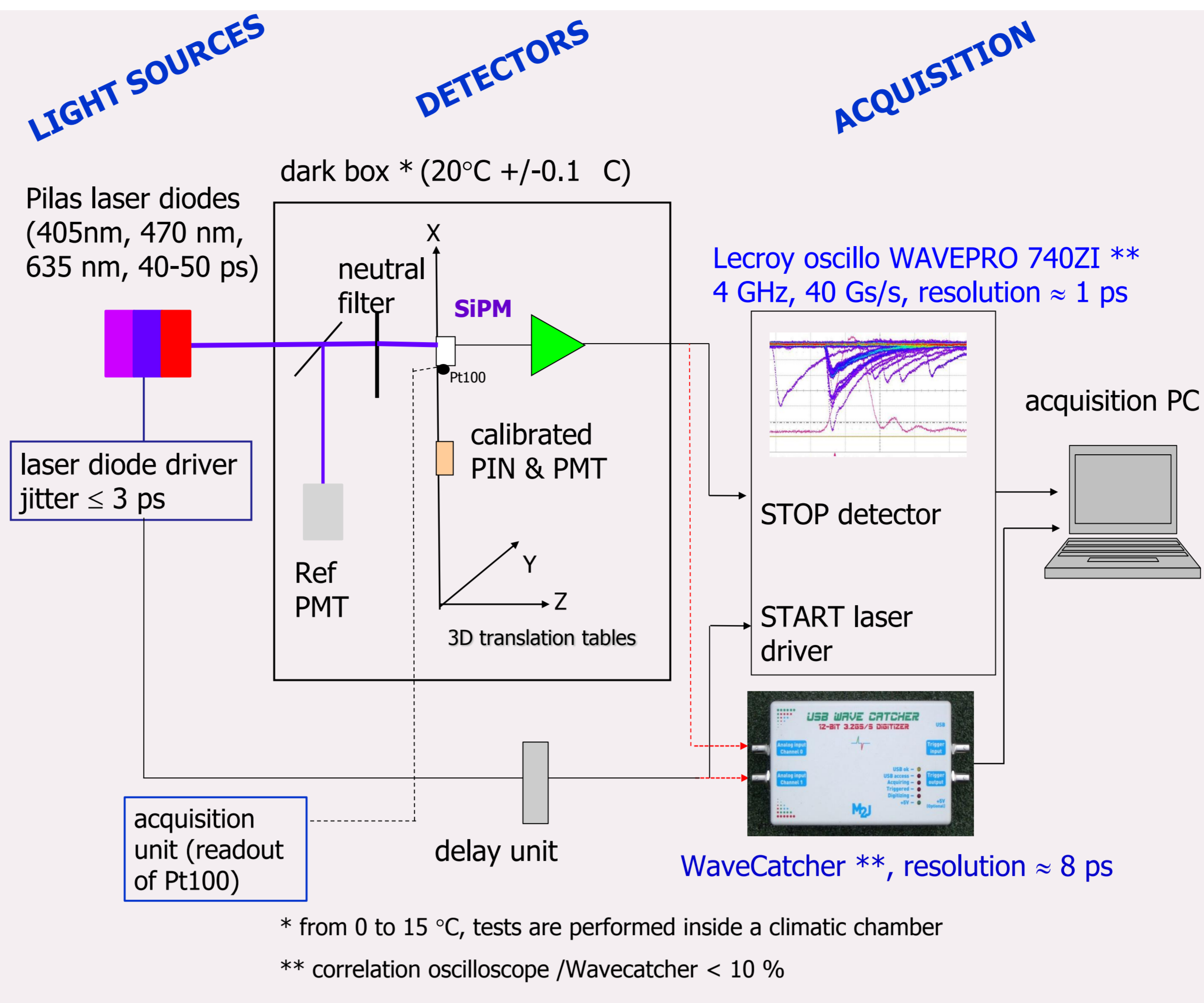
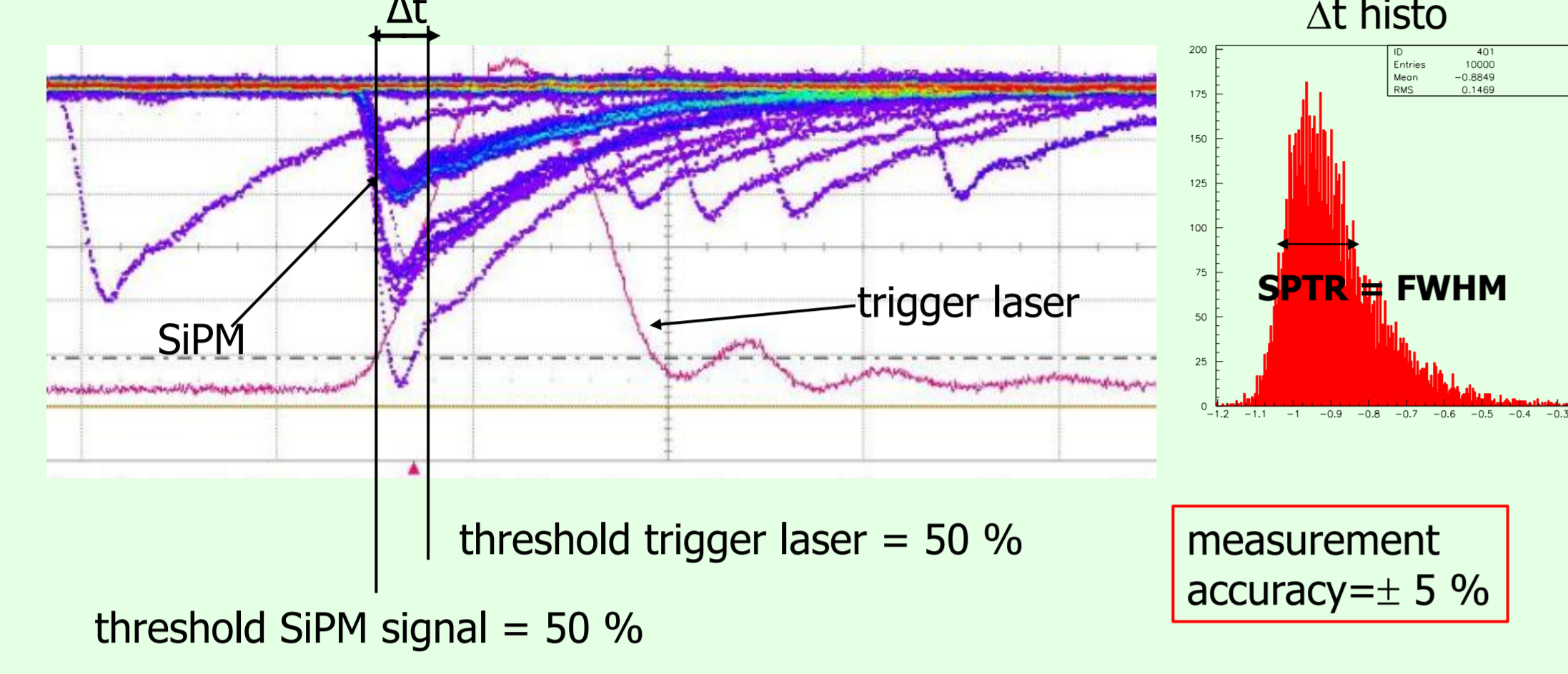


Study of the **SiPM Single Photoelectron Timing Resolution (SPTR)** variations with:

- ❖ the bias voltage
- ❖ the wavelength of the pulsed incident light : 405 - 467 - 635 nm
- ❖ the temperature : 0°C to 20 °C

Measurement principle: measurement of the difference of time (Δt) between the laser trigger signal and the SiPM signal (at the amplifier output) \rightarrow histogram of $\Delta t \rightarrow$ SPTR = FWHM



List of the studied SiPMs (1 and 9 mm²)

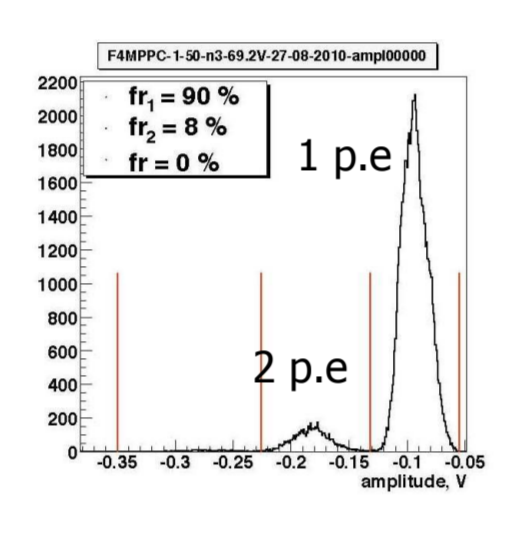
Producer	Ref SiPM	pixel size (μm)	V _{BD} (V)
AdvanSiD	ASD-1S-M-50	50x50	29
HAMAMATSU	S10362-11-25	25x25	69,2
HAMAMATSU	S10362-11-50	50x50	68,3
HAMAMATSU	S10362-11-100	100x100	68,7
HAMAMATSU	MPPC-10-50S	50x50	69,1
HAMAMATSU	MPPC-10-100S	100x100	69,1
Sensl	SPM1020X13	20x20	27
Sensl	SPM1035X13	35x35	27,5
AdvanSiD	ASD-3S-M-50	50x50	31
HAMAMATSU	S10362-33-25	25x25	69,5
HAMAMATSU	S10362-33-50	50x50	69,5
HAMAMATSU	S10362-33-100	100x100	69,2
Sensl	SPM3035X13	35x35	27

Full characterization of the SiPMs:

Before measuring the SPTR, each SiPM is characterized : breakdown voltage (V_{BD}), gain, dark count rate (DCR) as a function of the temperature \rightarrow adaptation of bias voltage with the temperature in order to keep V_{BD} constant

Illumination conditions:

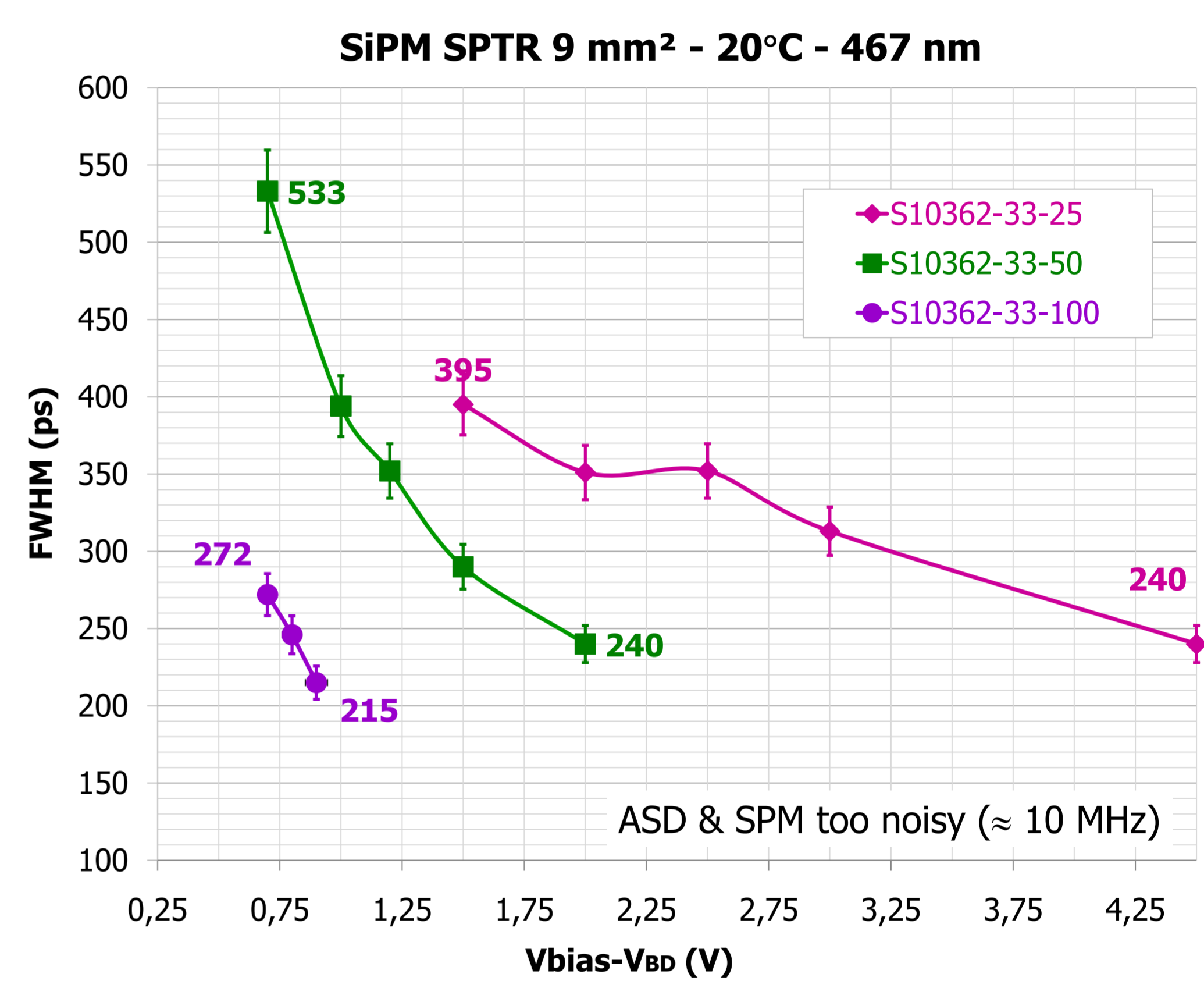
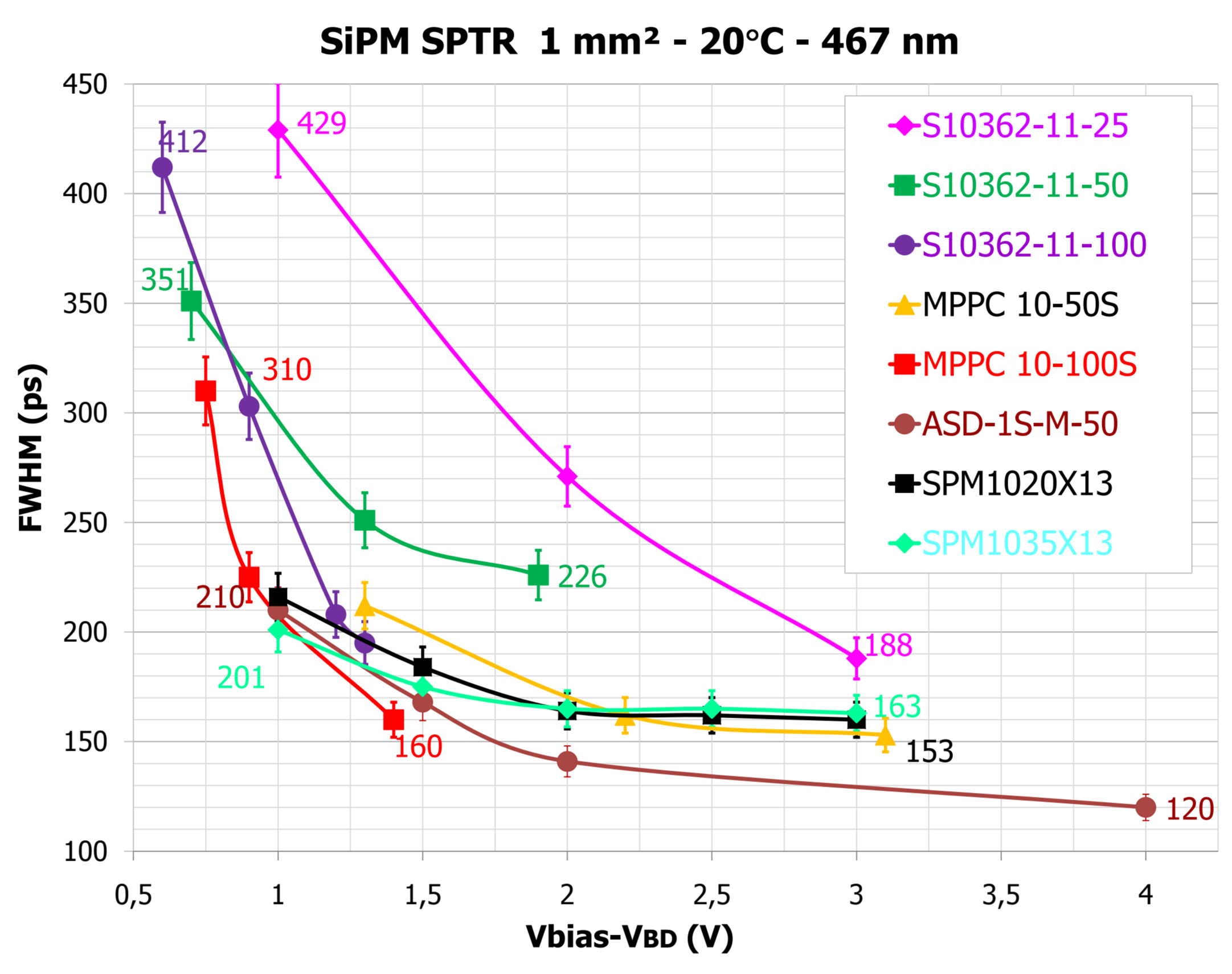
Very low light flux \approx 1-2 photons/pulse \rightarrow at the SiPM output: majority of 0, few pulses α 1 p.e., very few signal α 2 p.e. (SiPM cross-talk)



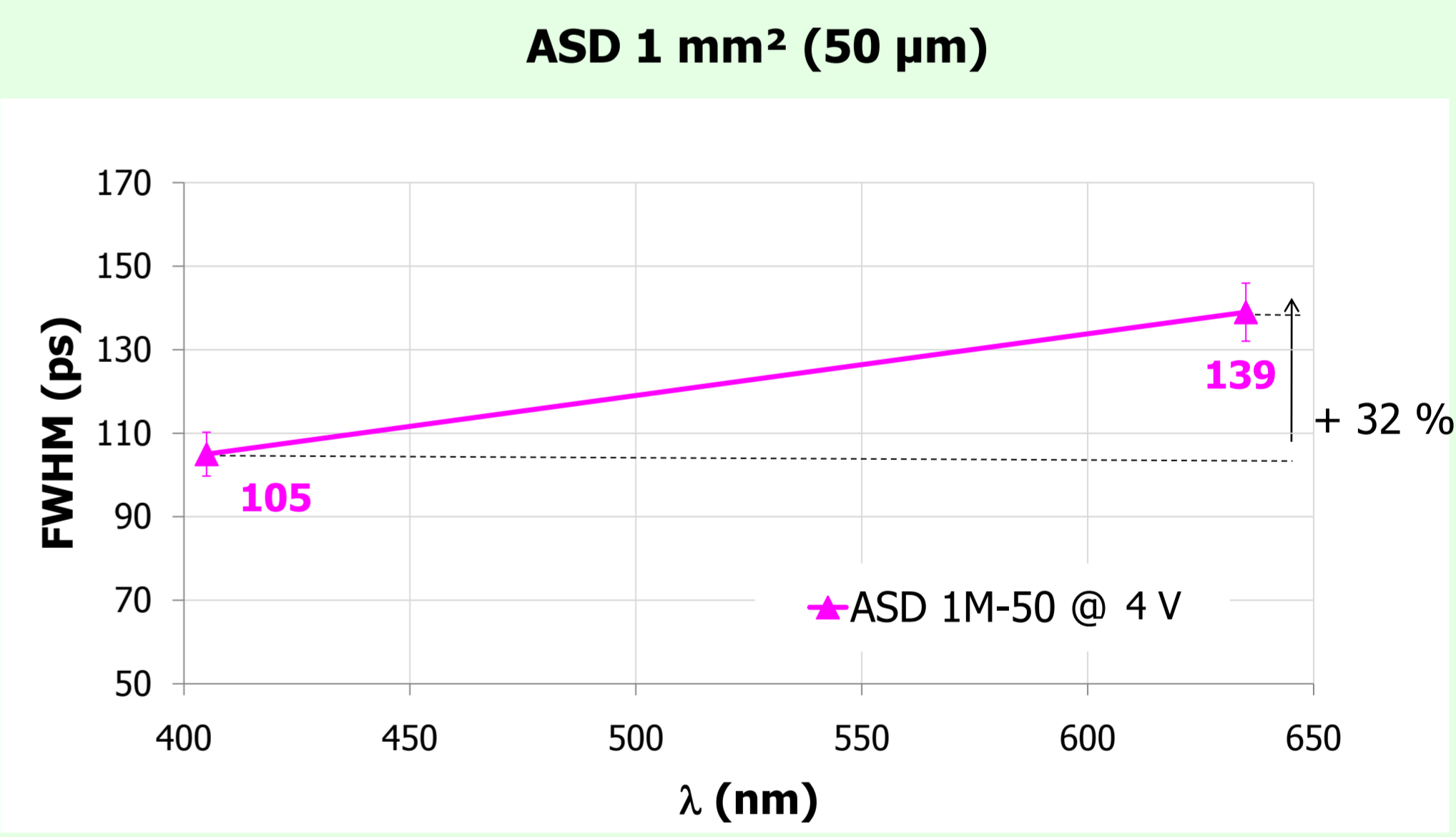
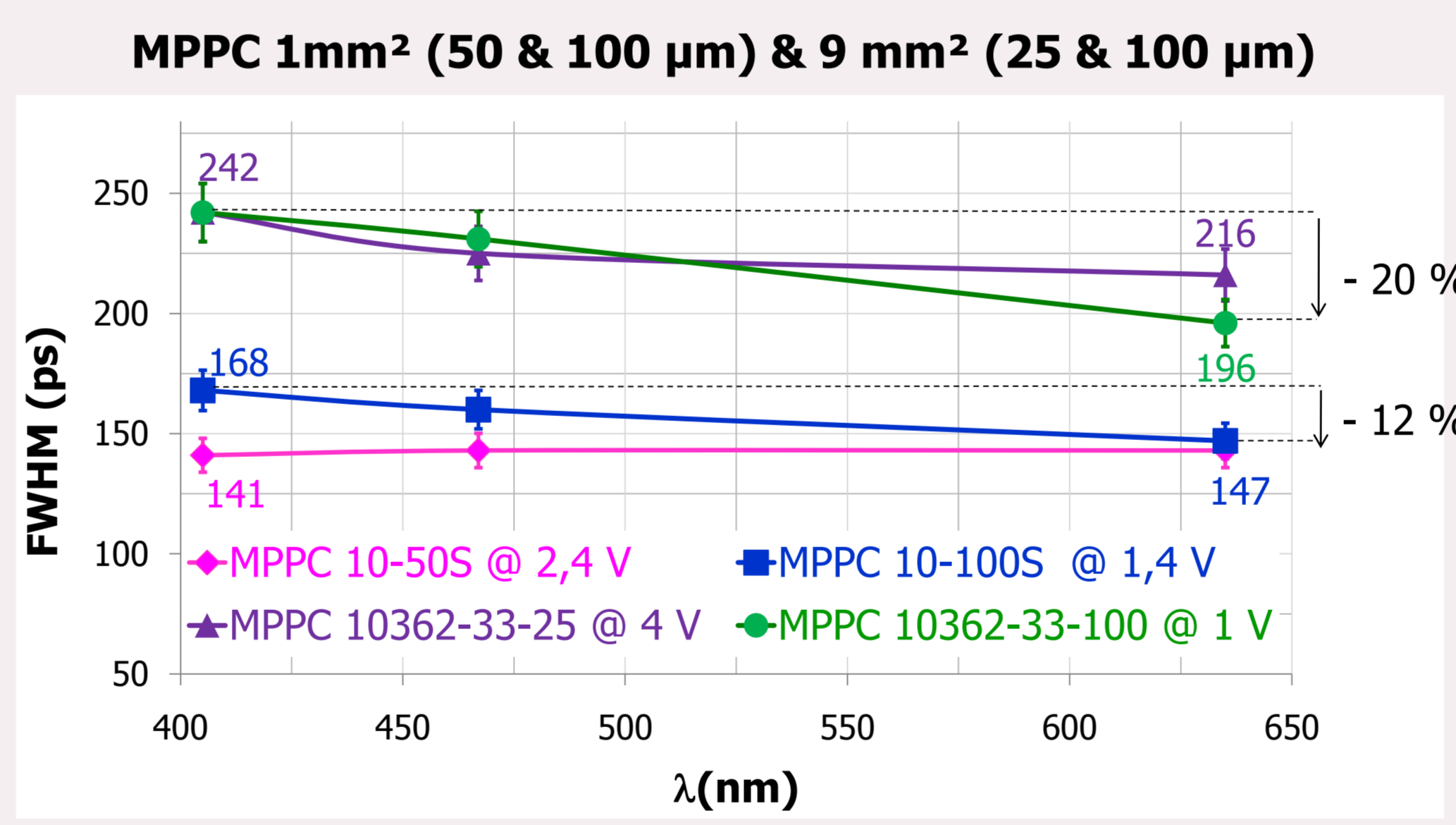
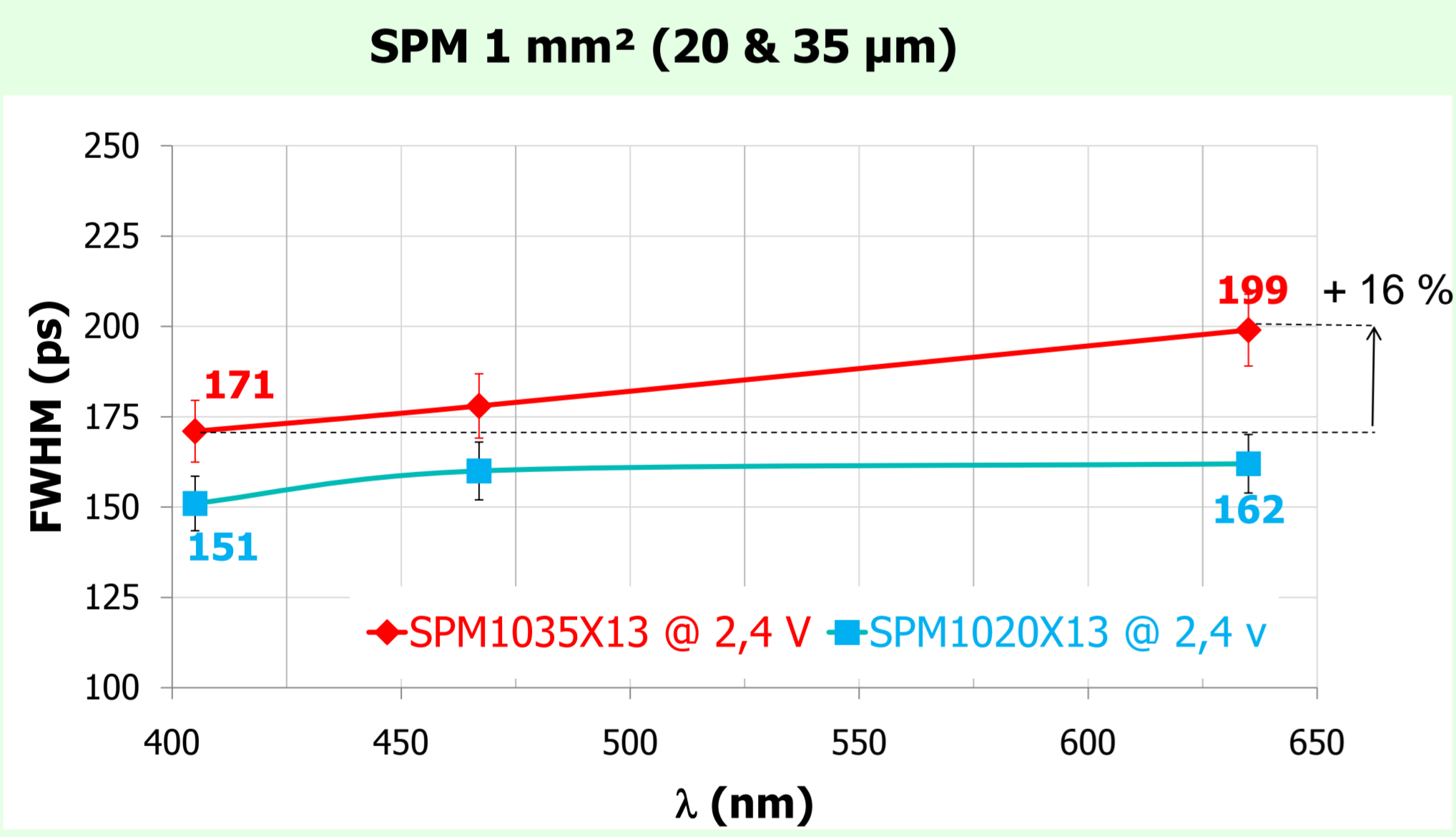
Contribution to the timing resolution:

- laser jitter \leq 3 ps
- 40 ps < laser pulse width < 50 ps
- timing resolution of the Wavecatcher \approx 8 ps
- timing resolution of the oscilloscope \approx 1 ps

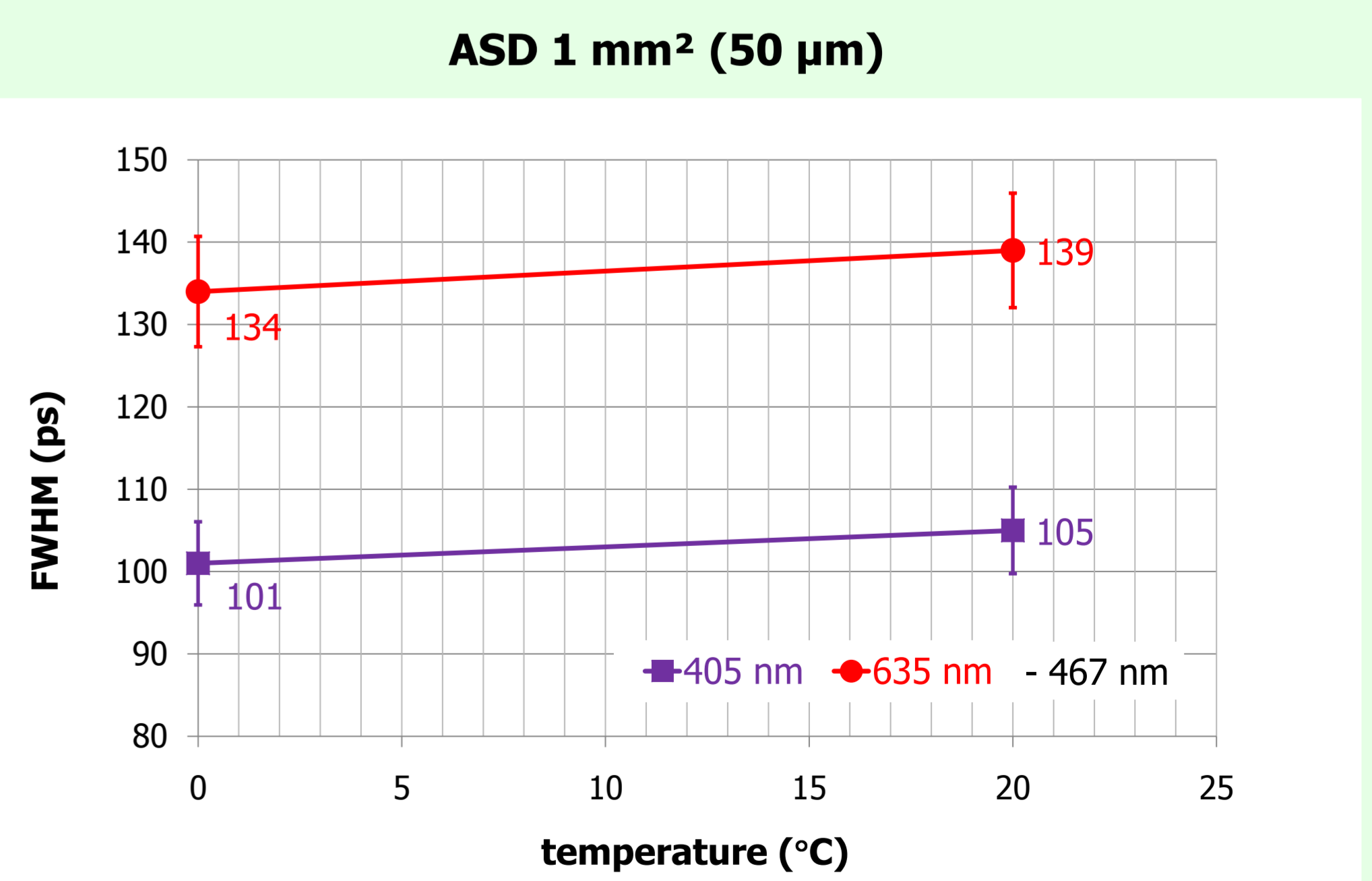
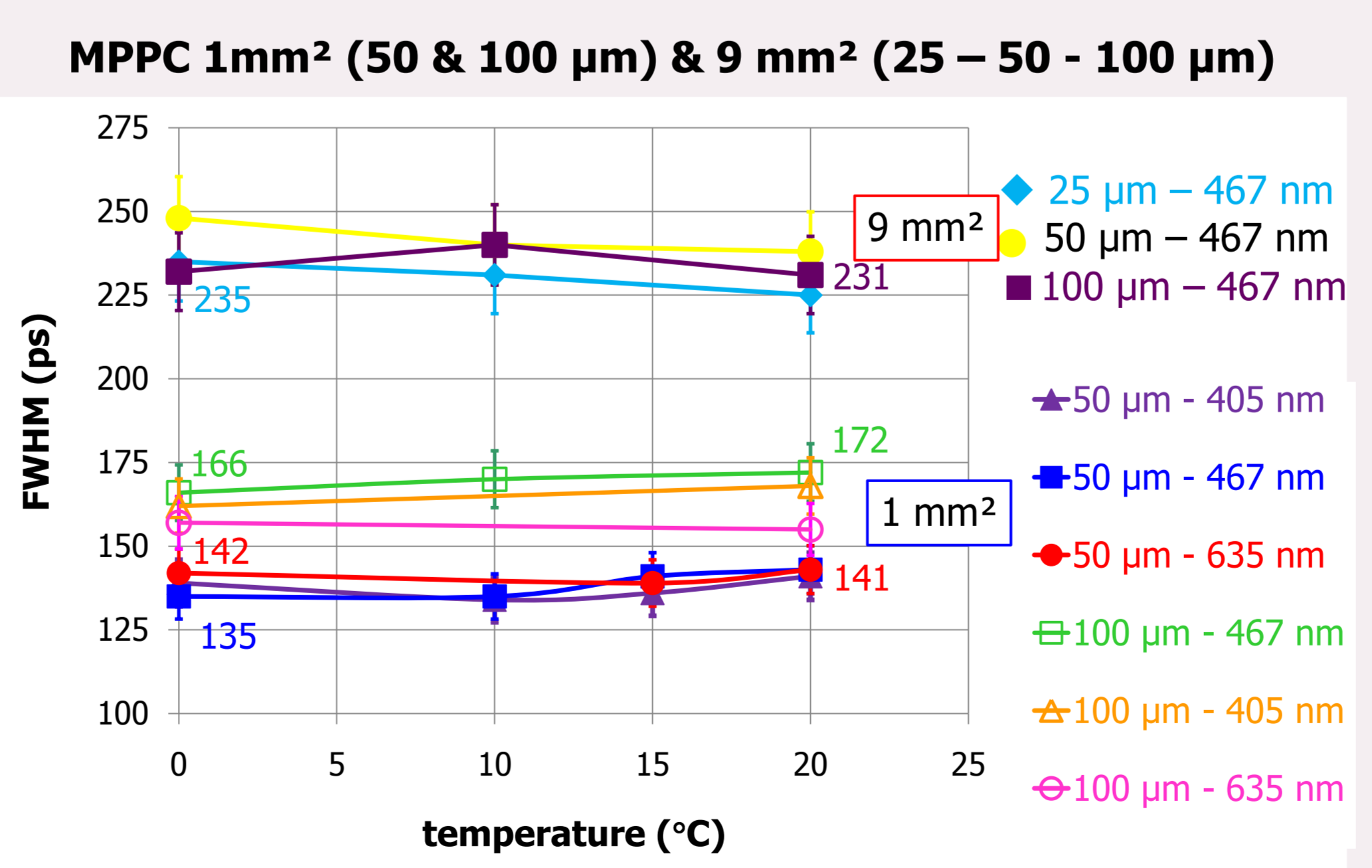
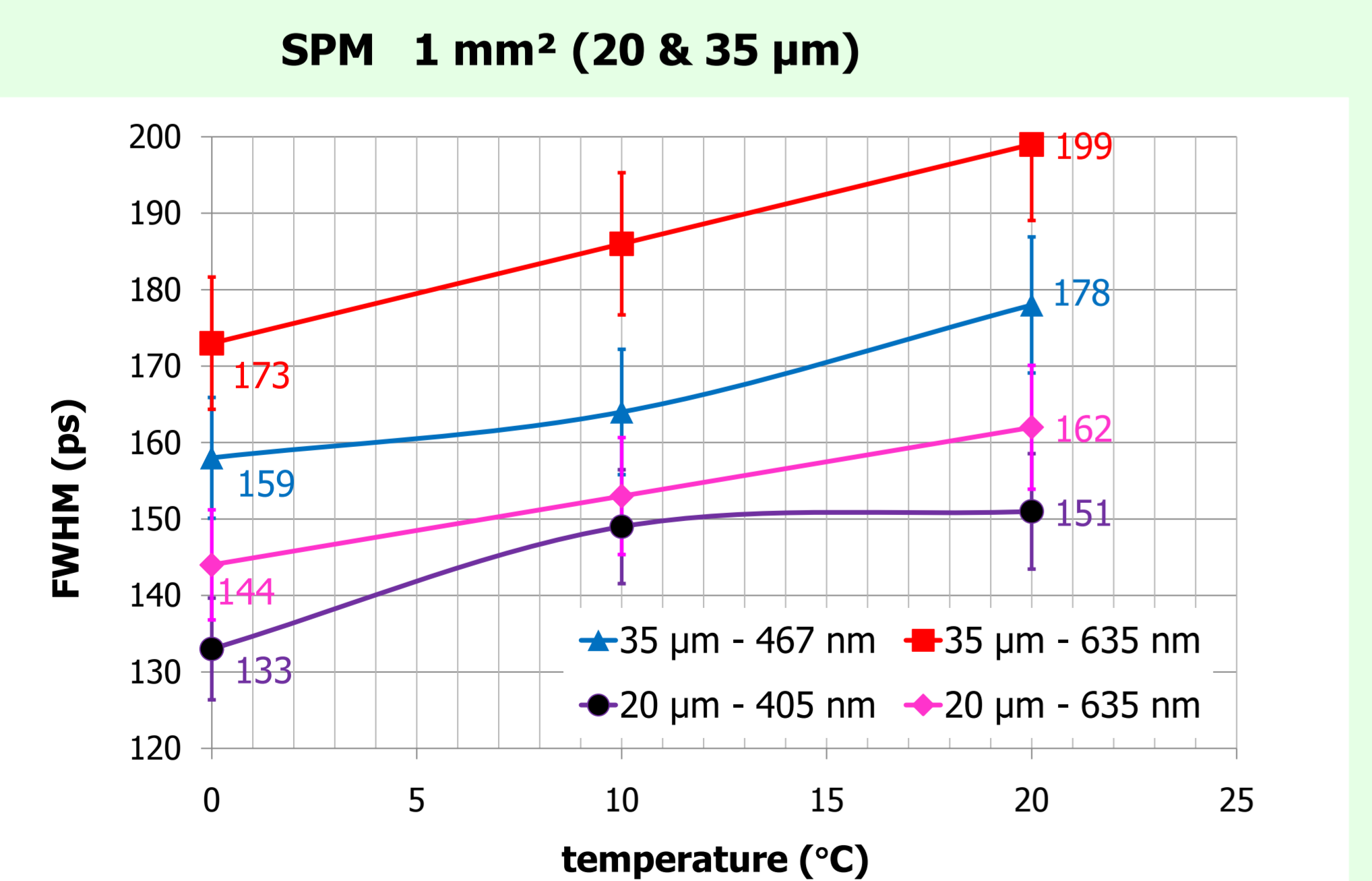
Study of the SPTR variation as a function of the bias voltage



Study of the SPTR variation as a function of the wavelength at 20 °C and with Vbias max (above this value the timing resolution is difficult to measure due to the high DCR)



Study of the SPTR variation as a function of the temperature at ΔV (Vbias - Vbd) constant (temperature stability = ± 0.1 °C)



Summary

SPTR variation with the bias voltage

Improvement of the SPTR with the increasing of the bias voltage

Best SPTR @ 467 nm & 20°C

1 mm² : 120 ps (FWHM)
9 mm² : 215 ps (FWHM)

SPTR variation with the wavelength

405 nm \rightarrow 635 nm

- SPM: small degradation (5 %-15 %)
- MPPC: small improvement: 5- 10 % for 1 mm², 10 - 20 % for 9 mm²
- ASD: degradation (30 %)

SPTR variation with the temperature

0°C temperature \rightarrow 20°C

- ❖ SPM: small degradation (5-15 %)
- ❖ MPPC: stable for 1 and 9 mm²
- ❖ ASD: stable

Work still under study

Explanation of :

- the timing distribution shape
- the SPTR differences between 2 SiPMs of the same kind but with different pixel size
- the SPTR variation with the temperature